## **CLAIMS**

- 1 1. A wafer having a plurality of devices being fabricated thereupon, wherein said
- 2 wafer is configured to undergo a chemical mechanical polishing (CMP) step on a surface
- 3 of the wafer comprising:
- a plurality of arrays wherein each array includes a plurality of test features that
- 5 project from the wafer surface to be polished, wherein each projecting test feature is
- 6 formed with a relatively hard upper surface layer; and
- wherein the plurality of projecting test features within an array have an identical
- 8 diameter, and wherein the diameter of the projecting test features of each different array
- 9 differs.
- 1 2. A wafer as described in claim 1, wherein said upper surface layer is comprised of
- 2 diamond-like-carbon (DLC).
- 1 3. A wafer as described in claim 1, wherein each said projecting test feature has a
- 2 diameter that is less than approximately 5 µm.
- 1 4. A wafer as described in claim 1, wherein each said array is formed with an array
- 2 area of at least approximately  $400 \mu m^2$ .

- 1 5. A wafer as described in claim 1, wherein each said array is formed of sufficient
- 2 size to be viewable with an optical microscope, where the projecting test features within
- 3 each array are too small to be viewable with an optical microscope.
- 1 6. A wafer as described in claim 1, wherein the diameter of the projecting test
- 2 features within an array is associated with a known polishing time in which said upper
- 3 surface layer of the test feature is removed by the polishing process.
- 1 7. A wafer as described in claim 6, wherein the different diameter of the projecting
- 2 test features of each differing array corresponds to a particular polishing time increment.
- 1 8. A wafer as described in claim 7, wherein said polishing time increment is five
- 2 seconds.
- 1 9. A wafer as described in claim 1, wherein said group of arrays includes nine
- 2 arrays.
- 1 10. A wafer as described in claim 1, wherein each array within a group of arrays
- 2 includes a unique identification symbol associated therewith.
- 1 11. A wafer as described in claim 1, wherein each array includes a plurality of
- 2 projecting test features that are arranged in a plurality of rows and columns.

- 3 12. A process for fabricating a magnetic head upon a wafer surface, including a
- 4 chemical mechanical polishing (CMP) process step, comprising:
- forming a plurality of arrays upon a wafer surface, wherein each array includes a
- 6 plurality of test features that project from the wafer surface to be polished, wherein each
- 7 projecting test feature is formed with a relatively hard upper surface layer, wherein each
- 8 said array includes a plurality of projecting test features having an identical diameter, and
- 9 wherein the diameter of the projecting test features of each array differs;
- polishing the wafer surface in a CMP step;
- checking the progress of the CMP step by examining the wafer surface with an
- optical microscope to determine which of the arrays includes test features in which the
- upper surface layer of the test features has been removed by the CMP polishing; and
- stopping said CMP step when it is seen through the optical microscope that test
- 15 features of a previously determined array have had their upper surface removed.
- 1 13. A process for fabricating a magnetic head as described in claim 12, wherein said
- 2 upper surface layer is comprised of diamond-like-carbon (DLC).
- 1 14. A process for fabricating a magnetic head as described in claim 12, wherein each
- 2 said projecting test feature has an effective diameter that is less than approximately 5 μm.
- 1 15. A process for fabricating a magnetic head as described in claim 12, including
- forming each said array with an array area of at least approximately  $400 \mu m^2$ .

- 1 16. A process for fabricating a magnetic head as described in claim 12, including
- 2 forming each said array of sufficient size to be viewable with an optical microscope,
- 3 where the projecting test features within each array are too small to be viewable with an
- 4 optical microscope.
- 1 17. A process for fabricating a magnetic head as described in claim 12, including
- 2 forming the diameter of the projecting test features within an array to be associated with a
- 3 known polishing time in which said upper surface layer of the test feature is removed by
- 4 the polishing process.
- 1 18. A process for fabricating a magnetic head as described in claim 17, including
- 2 forming the different diameter of the projecting test features of each differing array to
- 3 correspond to a particular polishing time increment.
- 1 19. A process for fabricating a magnetic head as described in claim 18, wherein said
- 2 polishing time increment is five seconds.
- 1 20. A process for fabricating a magnetic head as described in claim 12, including
- 2 forming said group of arrays to include nine arrays.
- 1 21. A process for fabricating a magnetic head as described in claim 12, wherein each
- 2 array within a group of arrays is formed with a unique identification symbol.

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- 1 22. A process for fabricating a magnetic head as described in claim 12, wherein each
- 2 array includes a plurality of projecting test features that are arranged in a plurality of
- 3 rows and columns.

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